Talks and Conference Contributions

[1] K.J. Ebeling and R. Michalzik, "VCSEL research at Ulm revisited", *International Symposium on VCSELs and Integrated Photonics — Celebrating the 30th Anniversary of VCSEL*. Tokyo, Japan, Dec. 2007.

[2] J. Hertkorn, P. Brückner, S. B. Thapa, T. Wunderer, F. Scholz, M. Feneberg, K. Thonke, R. Sauer, M. Beer, and J. Zweck, "Optimization of nucleation and buffer layer growth for improved GaN quality and device performance", poster at *12th European Workshop on MOVPE*, Bratislava, Slovakia, June 2007.

[3] J. Hertkorn, P. Brückner, C. Gao, and F. Scholz, "Transport properties in n-type AlGaN/AlN/GaN-superlattices", poster at *7th Int. Conf. on Nitride Semiconductors*, Las Vegas, Nevada, USA, Sept. 2007.

[4] J. Hertkorn, "Modulation doped AlGaN/(AlN)/GaN heterostructures for high brightness LEDs", New Jersey Institute of Technology, Newark, NJ, USA, Oct. 2007.

[5] J. Hertkorn, "Modulation doped n- and p-type AlGaN/(AlN)/GaN heterostructures for improved current spreading in high power LEDs", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[6] J. Hertkorn, "Modulation doped AlGaN/(AlN)/GaN heterostructures for high brightness LEDs", Seminar *"Neue Materialien"*, Universitt Magdeburg, Nov. 2007.

[7] A. Kroner, F. Rinaldi, R. Rösch, and R. Michalzik, "Densely packed VCSEL arrays tailored for optical particle manipulation", *Conf. on Lasers and Electro-Optics Europe, CLEO/Europe 2007*, paper CB4-1-TUE. Munich, Germany, June 2007.

[8] F. Lipski, "Freestanding GaN by HVPE", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[9] F. Lipski, P. Brückner, and F. Scholz, "Si-Dotierung von GaN-Schichten bei der Hydrid-Gasphasen-Epitaxie", *DGKK-Workshop III-V-Epitaxie*, Marburg, Germany, Dec. 2007.

[10] R. Michalzik, "Vertical-cavity surface-emitting lasers for optical interconnection" (in German), *Electrical Engineering Colloquium*, Ulm University, Faculty of Engineering and Computer Sciences, Ulm, Germany, July 2007.

[11] R. Michalzik, M. Stach, F. Rinaldi, and S. Lorch, "Novel VCSEL-based transceiver chips for bidirectional optical interconnects using butt-coupled multimode fibers", in Proc. 5. ITG-Workshop *Photonische Aufbau- und Verbindungstechnik*, pp. 33–37. Berlin, Germany, Mar. 2007.

[12] R. Michalzik, M. Stach, F. Rinaldi, and S. Lorch, "Monolithic integration of VCSELs and MSM photodiodes for bidirectional multimode fiber communications" (invited), *SPIE Photonics West 2007*, Conf. on *Vertical-Cavity Surface-Emitting Lasers XI*. San Jose, CA, USA, Jan. 2007.

[13] J.M. Ostermann, P. Debernardi, and R. Michalzik, "Polarization stability of surface grating VCSELs under strong optical feedback", *Conf. on Lasers and Electro-Optics Europe, CLEO/Europe 2007*, paper CB7-1-WED. Munich, Germany, June 2007.

[14] F. Rinaldi and D. Wahl, "MBE technology II", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[15] F. Rinaldi, S. Li, S. Menzel, and D. Wahl, "Characterization of MBE grown VCSELs", *Deutscher MBE Workshop 2007*, Jülich, Germany, Oct. 2007.

[16] H. Roscher, F. Rinaldi, A. Weigl, and R. Michalzik, "Record-low thermal resistance, 12.5 Gbit/s capable flip-chip bonded 850 nm wavelength 2-D VCSEL arrays", *Conf. on Lasers and Electro-Optics Europe, CLEO/Europe 2007*, paper CB4-4-TUE. Munich, Germany, June 2007.

[17] S. Schwaiger, "Influence of strain on magnetic anisotropy in GaMnAs", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[18] F. Scholz, "LEDs: Basic concepts and state of the art", Lumitronix, Hechingen, Germany, Apr. 2007.

[19] F. Scholz, S. B. Thapa, and E. Angelopoulos, "Heteroepitaxial growth of GaN on ZnO by MOVPE", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[20] W. Schwarz, "Approaches for vertical extended cavity lasers", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[21] M. Stach, F. Rinaldi, J. Scharpf, S. Lorch, and R. Michalzik, "1 Gbit/s bidirectional optical data transmission over 50 m semi-GI PCS fiber with monolithically integrated transceiver chips", *EOS Conf. on Trends in Optoelectronics, Sub-conf. on Information and Communication*. Munich, Germany, June 2007.

[22] M. Stach, F. Rinaldi, D. Wahl, D. Rimpf, S. Lorch, and R. Michalzik, "1 Gbit/s full-duplex bidirectional optical data transmission over 500 m of 50 μm-core graded-index multimode fiber with novel monolithically integrated transceiver chips", *33rd Europ. Conf. on Opt. Commun., ECOC 2007*. Berlin, Germany, Sept. 2007.

[23] M. Stach, F. Rinaldi, D. Wahl, D. Rimpf, S. Lorch, and R. Michalzik, "Monolithically integrated miniaturized transceiver chips for bidirectional graded-index fiber systems" (in German: "Monolithisch integrierte miniaturisierte Transceiver-Chips für bidirektionale Gradientenindexfaser-Systeme"), *14th ITG Symposium on Communication Cable Networks*, Köln, Germany, Dec. 2007.

[24] S.B. Thapa, and F. Scholz, "AlN Growth by MOVPE", *Georgia Tech Lorraine*, Metz, France, Feb. 2007.

[25] S.B. Thapa, J. Hertkorn, F. Scholz, G.M. Prinz, M. Feneberg, K. Thonke, and R. Sauer, "MOVPE Growth of High Quality AlN Layers and Effects of Si doping", poster at *12th European Workshop on MOVPE*, Bratislava, Slovakia, June 2007.

[26] S.B. Thapa, E. Angelopoulos, J. Hertkorn, F. Scholz, A. Reiser, K. Thonke, R. Sauer, H. Hochmuth, M. Lorenz, and M. Grundmann, "Heteroepitaxial Growth of GaN on ZnO by MOVPE" poster at *12th European Workshop on MOVPE*, Bratislava, Slovakia, June 2007.

[27] S.B. Thapa, F. Scholz, J. Hertkorn, G.M. Prinz, M. Feneberg, K. Thonke, and R. Sauer, "MOVPE Growth of High Quality AlN Layers and Effects of Si doping", *7th Int. Conf. on Nitride Semiconductors*, Las Vegas, Nevada, USA, Sept. 2007.

[28] S.B. Thapa, "MOVPE Growth of High Quality AlN Layers and Effects of Si doping", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[29] D. Wahl and F. Rinaldi, "MBE technology I", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[30] T. Wunderer, F. Lipski, J. Hertkorn, P. Brückner, F. Scholz, M. Feneberg, M. Schirra, K. Thonke, A. Chuvilin, and U. Kaiser, "Bluish-green semipolar GaInN/GaN light emitting diode on $\{1\bar{1}01\}$ GaN side facets", poster at *7th Int. Conf. on Nitride Semiconductors*, Las Vegas, Nevada, USA, Sept. 2007.

[31] T. Wunderer, "Steps to the green LED", *Söllerhaus-Seminar*, Riezlern, Austria, Oct. 2007.

[32] T. Wunderer, "High-brightness GaN-based light emitting diodes", Physical Institute at Lomonosov Moscow State University, Moscow, Russia, Nov. 2007.

[33] T. Wunderer, F. Lipski, J. Hertkorn, P. Brückner, F. Scholz, M. Feneberg, M. Schirra, K. Thonke, A. Chuvilin, U. Kaiser, I. Knoke, and E. Meissner, "Blau-grüne semipolare GaInN/GaN LEDs auf $\{1\bar{1}01\}$ GaN-Seitenfacetten", *DGKK-Workshop III-V-Epitaxie*, Marburg, Germany, Dec. 2007.

[34] M.V. Klymenko, I.M. Safonov, O.V. Shulika, I.A. Sukhoivanov, and R. Michalzik, "Effective-mass superlattice as an injector in quantum cascade lasers", *International Workshop on PHysics & Applications of SEmiconductor Lasers, PHASE 2007.* Supélec, Campus de Metz, Metz, France, March 2007.

[35] B. Scherer, J. Wöllenstein, M. Weidemüller, W. Salzmann, J.M. Ostermann, F. Rinaldi, and R. Michalzik, "Oxygen measurements at high pressures using a low cost, polarization stabilized, widely tunable vertical-cavity surface-emitting laser", *SPIE Europe, Microtechnologies for the New Millennium*, Conf. on *Smart Sensors, Actuators and MEMS III.* Maspalomas, Gran Canaria, Spain, May 2007.